CLAIMS

What is claimed is:

1. A method comprising:

applying a photoresist layer to a first wafer substrate (wafer);

etching the first wafer;

bonding the first wafer to a second wafer; and

thinning the first wafer to remove an unsupported bevel portion of the first wafer.

2. The method of claim 1 further comprising stripping the photoresist layer after the first wafer has been etched.

3. The method of claim 1 wherein the photoresist layer is applied to protect an active portion of the first wafer.

4. The method of claim 1 wherein the first wafer is etched using a dry etching method.

5. The method of claim 1 wherein the first wafer is etched using a wet etching method.

6. The method of claim 1 wherein thinning the first wafer comprises grinding the first wafer.

7. A method comprising:

applying a photoresist layer to a first wafer to cover a first component of the first wafer substrate (wafer);

etching the first wafer;

bonding the first component of the first wafer to a second wafer; and

thinning the first wafer to remove a second unsupported component of the first wafer.

8. The method of claim 7 further comprising stripping the photoresist layer from the first component after the first wafer has been etched.

9. The method of claim 7 wherein the first wafer is etched using a dry etching method.

10. The method of claim 7 wherein the first wafer is etched using a wet etching method.

11. The method of claim 7 wherein thinning the first wafer comprises grinding the first wafer.

12. A method comprising:

removing a first portion of an unsupported component from a wafer substrate (wafer);

bonding an active component of the first wafer to a second wafer; and

thinning the first wafer to remove a second portion of the unsupported component of the first wafer.

13. The method of claim 12 wherein removing the first portion of the unsupported component comprises:

applying a photoresist layer to cover the active component of the first wafer;

etching the first portion of the unsupported component of the first wafer;

14. The method of claim 13 further comprising stripping the photoresist layer from the first component after the first wafer has been etched.

15. The method of claim 12 wherein thinning the first wafer comprises grinding the first wafer.